



NEC

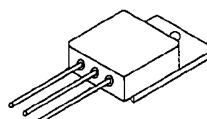
NEW ENGLAND SEMICONDUCTOR

NSFY140

POWER MOSFET N CHANNEL

- REPETITIVE AVALANCHE RATINGS
- LOW $R_{DS(ON)}$
- LOW DRIVE REQUIREMENT
- DYNAMIC dv/dt RATING

TO-257AA



18 AMPERE

100 VOLTS

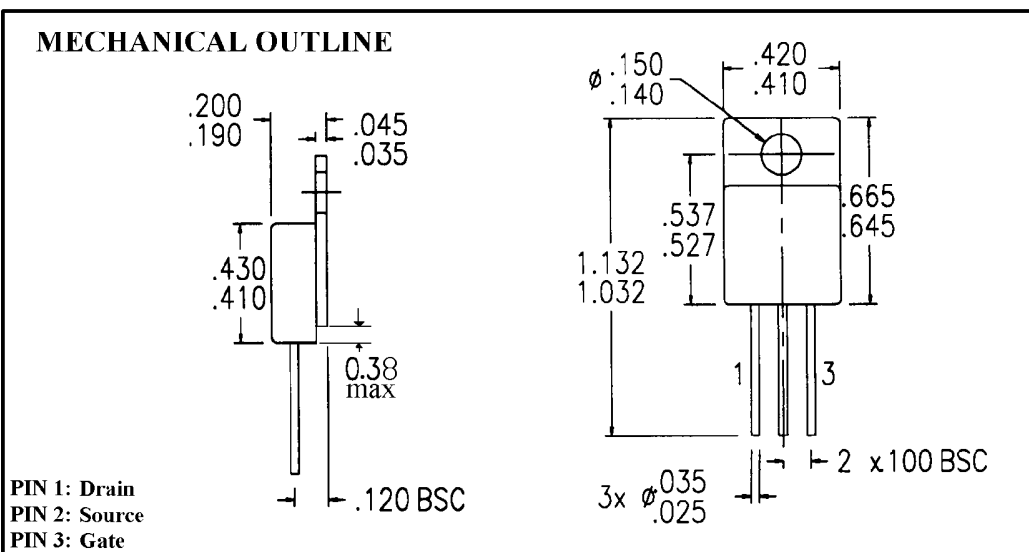
0.095 Ω

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

PARAMETERS / TEST CONDITIONS		SYMBOL	VALUE	UNITS
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C = 25^\circ\text{C}$	I_D	18	A
Pulsed Drain Current (1)		I_{DM}	72	A
Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	60	W
Operating Junction & Storage Temperature Range		T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

(1) Pulse width limited by maximum junction temperature.

MECHANICAL OUTLINE



NEW ENGLAND SEMICONDUCTOR

6 Lake Street Lawrence, MA 01841
1-800-446-1158 / (978) 794-1666 / FAX: (978) 689-0803

T4-4.8-860-937 REV: --

**NES****NEW ENGLAND SEMICONDUCTOR****NSFY140****ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}\text{C}$ unless otherwise noted)**

PARAMETERS / TEST CONDITIONS		SYMBOL	MIN.	TYP.	MAX.	UNITS
Drain-Source Breakdown Voltage $V_{GS} = 0\text{ V}, I_D = 1.0\text{ mA}$		$V_{(BR)DSS}$	100			V
Gate Threshold Voltage $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		$V_{GS(th)}$	2.0		4.0	V
Zero Gate Voltage Drain Current $V_{DS} = 0.8\text{ max Rating}, V_{GS} = 0\text{ V}$		I_{DSS}			25	μA
Zero Gate Voltage Drain Current $V_{DS} = 80\% \text{ max } V_{(BR)DSS}, V_{GS} = 0\text{ V}, T_J = 125^{\circ}\text{C}$		I_{DSS}			250	μA
Drain-Source On-State Resistance (2) $V_{GS} = 10\text{ V}, I_D = 60\% \text{ Rated } I_D$		$r_{DS(on)}$			0.095	Ω
Forward Transconductance (2) $V_{DS} = 15\text{ V}, I_D = 12\text{ A}$ ($V_{DS} \geq I_{D(ON)} \times R_{DS(ON)} \text{ max}$)		g_{fs}	9.1			S(Ω)
Input Capacitance	$V_{GS} = 0\text{ V}$	C_{iss}		1660		pF
Output Capacitance	$V_{DS} = 25\text{ V}$	C_{oss}		550		
Reverse Transfer Capacitance	$f = 1.0\text{ MHz}$	C_{rss}		120		
Total Gate Charge	$V_{DS} = 0.5 V_{DS}$ $V_{GS} = 10\text{ V}, I_D = 18\text{ A}$ (Gate charge is essentially independent of operating temperature.)	Q_g	30		59	nC
Gate-Source Charge		Q_{gs}	2.4		12	
Gate -Drain Charge		Q_{gd}	12		30.7	
Turn-On Delay Time	$V_{dd} = 50\% V_{DS},$ $I_D = 18\text{ A},$ $R_G = 9.1\text{ }\Omega$ (Switching time is essentially independent of operating temperature.)	$t_{d(on)}$			21	ns
Rise Time		t_r			145	
Turn-Off Delay Time		$t_{d(off)}$			64	
Fall Time		t_f			105	

SOURCE-DRAIN DIODE RATINGS & CHARACTERISTICS ($T_J = 25^{\circ}\text{C}$ unless otherwise noted)

PARAMETERS / TEST CONDITIONS		SYMBOL	MIN.	TYP.	MAX.	UNITS
Continuous Current		I_S			18	A
Pulsed Current (1)		I_{SM}			73	A
Forward Voltage (2) $I_F = I_S, V_{GS} = 0\text{ V}$		V_{SD}			1.5	V
Reverse Recovery Time $I_F = I_S, di/dt = 100\text{ A}/\mu\text{S}, V_{DD} = 50\text{ V}$		t_{rr}			400	ns
Reverse Recovered Charge $I_F = I_S, di/dt = 100\text{ A}/\mu\text{S}, V_{DD} = 50\text{ V}$		Q_{rr}			2.4	μC

(1) Pulsed width limited by maximum junction temperature.

(2) Pulse Test: Pulse width < 300 μsec . Duty cycle $\leq 2\%$.**NEW ENGLAND SEMICONDUCTOR**6 Lake Street Lawrence, MA 01841
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